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Renesas Electronics website: http://www.renesas.com

April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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### DATA SHEET

## RENESAS

## MOS FIELD EFFECT TRANSISTOR

# Phase-out/Discontinued

## 2SK2480

#### SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

#### DESCRIPTION

The 2SK2480 is N-Channel MOS Field Effect Transistor designed for high voltage switching applications.

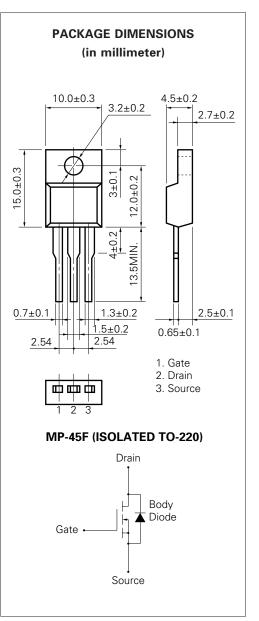
#### FEATURES

- Low On-Resistance
- RDS (on) = 4.0  $\Omega$  (VGS = 10 V, ID = 2.0 A)
- Low Ciss Ciss = 900 pF TYP.
- High Avalanche Capability Ratings
- Isolated TO-220 Package

#### ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

| Drain to Source Voltage                                    | Vdss        | 900         | V  |
|--|-------------|-------------|----|
| Gate to Source Voltage                                     | Vgss        | ±30         | V  |
| Drain Current (DC)   | D(DC)       | ±3.0        | А  |
| Drain Current (pulse)*                                     | D(pulse     | e) ±12      | А  |
| Total Power Dissipation (T <sub>c</sub> = 25 $^{\circ}$ C) | <b>P</b> T1 | 35          | W  |
| Total Power Dissipation (T <sub>A</sub> = 25 $^{\circ}$ C) | <b>P</b> T2 | 2.0         | W  |
| Channel Temperature  | Tch         | 150         | °C |
| Storage Temperature  | Tstg        | –55 to +150 | °C |
| Single Avalanche Current**                                 | las         | 3.0         | А  |
| Single Avalanche Energy**                                  | Eas         | 37.1        | mJ |
| * PW $\leq$ 10 $\mu$ s, Duty Cycle $\leq$ 1 %              |             |             |    |

\*\* Starting T<sub>ch</sub> = 25 °C, R<sub>G</sub> = 25  $\Omega$ , V<sub>GS</sub> = 20 V  $\rightarrow$  0

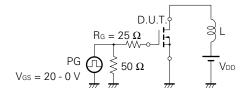


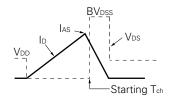
Phase-out/Discontinued

#### ELECTRICAL CHARACTERISTICS (TA = 25 $^{\circ}$ C)

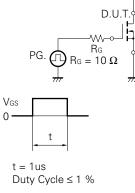
| CHARACTERISTIC                 | SYMBOL          | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS                                     |
|--------------------------------|-----------------|------|------|------|------|---|
| Drain to Source On-Resistance  | RDS (on)        |      | 3.2  | 4.0  | Ω    | $V_{GS} = 10 \text{ V}, \text{ Id} = 2.0 \text{ A}$ |
| Gate to Source Cutoff Voltage  | VGS (off)       | 2.5  |      | 3.5  | V    | $V_{DS} = 10 V, I_{D} = 1 mA$                       |
| Forward Transfer Admittance    | y <sub>fs</sub> | 1.0  |      |      | S    | $V_{DS} = 20 V, I_{D} = 2.0 A$                      |
| Drain Leakage Current          | Ibss            |      |      | 100  | μΑ   | $V_{DS} = V_{DSS}, V_{GS} = 0$                      |
| Gate to Source Leakage Current | Igss            |      |      | ±100 | nA   | $V_{GS} = \pm 30 \text{ V}, \text{ V}_{DS} = 0$     |
| Input Capacitance              | Ciss            |      | 900  |      | pF   | $V_{DS} = 10 V$                                     |
| Output Capacitance             | Coss            |      | 130  |      | pF   | Vgs = 0   |
| Reverse Transfer Capacitance   | Crss            |      | 25   |      | pF   | f = 1 MHz   |
| Turn-On Delay Time             | td (on)         |      | 17   |      | ns   | ID = 2.0 A  |
| Rise Time                      | tr              |      | 7    |      | ns   | $V_{GS} = 10 V$                                     |
| Turn-Off Delay Time            | td (off)        |      | 63   |      | ns   | $V_{DD} = 150 V$                                    |
| Fall Time                      | tr              |      | 8    |      | ns   | $R_G = 75 \ \Omega$                                 |
| Total Gate Charge              | Q <sub>G</sub>  |      | 30   |      | nC   | ID = 3.0 A  |
| Gate to Source Charge          | Qgs             |      | 5    |      | nC   | $V_{DD} = 450 V$                                    |
| Gate to Drain Charge           | Qgd             |      | 16   |      | nC   | Vgs = 10 V  |
| Body Diode Forward Voltage     | VF (S-D)        |      | 1.0  |      | V    | IF = 3.0 A, VGS = 0                                 |
| Reverse Recovery Time          | trr             |      | 650  |      | ns   | IF = 3.0 A, VGS = 0                                 |
| Reverse Recovery Charge        | Qrr             |      | 2.8  |      | μC   | di/dt = 50 A/µs                                     |

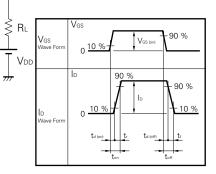
#### Test Circuit 1 Avalanche Capability



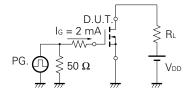


#### **Test Circuit 2 Switching Time**





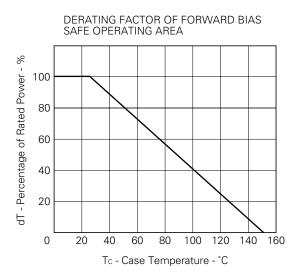
Test Circuit 3 Gate Charge

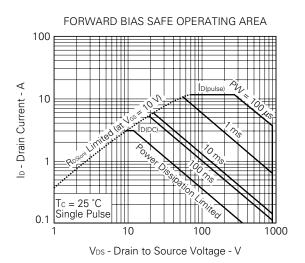


The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

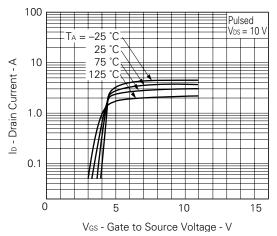
Phase-out/Discontinued

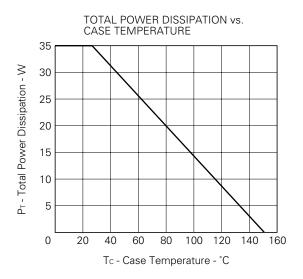




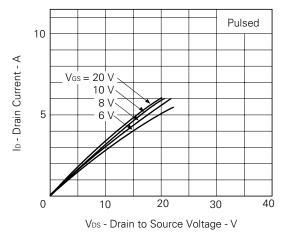


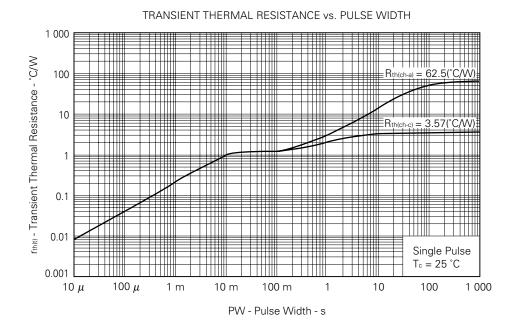
FORWARD TRANSFER CHARACTERISTICS





DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

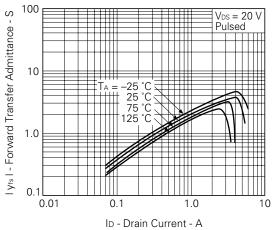


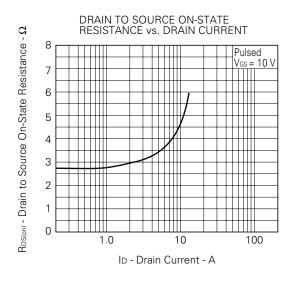


C

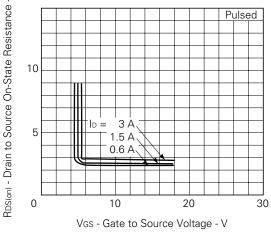
Phase-out/Discontinued



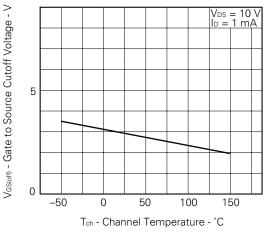




DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

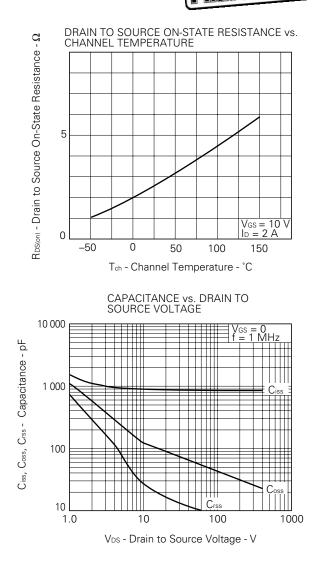


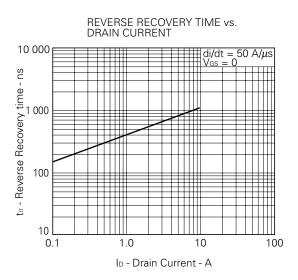
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE

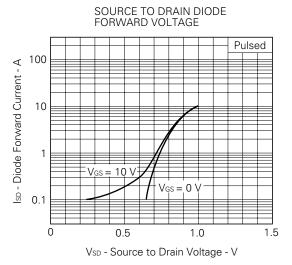


NEC

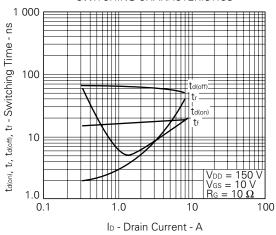
## Phase-out/Discontinued



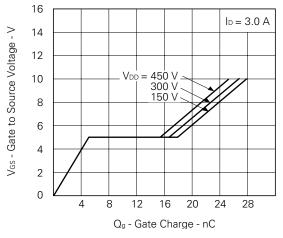




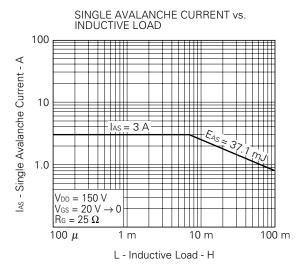
SWITCHING CHARACTERISTICS



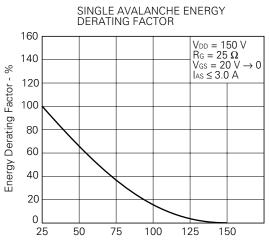
DYNAMIC INPUT/OUTPUT CHARACTERISTICS







NEC



Starting  $T_{ch}$  - Starting Channel Temperature -  $^{\circ}C$ 



#### REFERENCE

| Document Name  | Document No. |
|--|--------------|
| NEC semiconductor device reliability/quality control system.   | TEI-1202     |
| Quality grade on NEC semiconductor devices.                    | IEI-1209     |
| Semiconductor device mounting technology manual.               | IEI-1207     |
| Semiconductor device package manual.                           | IEI-1213     |
| Guide to quality assurance for semiconductor devices.          | MEI-1202     |
| Semiconductor selection guide.                                 | MF-1134      |
| Power MOS FET features and application switching power supply. | TEA-1034     |
| Application circuits using Power MOS FET.                      | TEA-1035     |
| Safe operating area of Power MOS FET.                          | TEA-1037     |

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